

EAST Search History**EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/581127	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 12:52
L2	2	("20050023642").PN.	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/06 12:53
L3	2	("20030146468").PN.	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/06 12:53
L4	2	("20030146477").PN.	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/06 12:53
L5	2	("20020168829").PN.	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/06 12:54
L6	2	("20030162360").PN.	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/06 12:54
L7	2	("20030219952").PN.	US_PGPUB; USPAT; USOOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/06 12:54

L8	2	("6222250").PN.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/06 12:54
L9	2	("4719185").PN.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/06 12:55
L10	2	9 and (complementary or bipolar or semiconductor or device or collector or emitter or base or region or npn or pnp or transistor or CMOS or FET or doping or type or conductivity or substrate or delimited or silicide or oxide or nitride or silicon or germanium or dry or etching or contact or bipolar)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 12:59
L11	2	8 and (complementary or bipolar or semiconductor or device or collector or emitter or base or region or npn or pnp or transistor or CMOS or FET or doping or type or conductivity or substrate or delimited or silicide or oxide or nitride or silicon or germanium or dry or etching or contact or bipolar)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:01
L12	1	"4940671".PN.	USPAT; USOCR	OR	ON	2010/06/06 13:04
L13	2	7 and (complementary or bipolar or semiconductor or device or collector or emitter or base or region or npn or pnp or transistor or CMOS or FET or doping or type or conductivity or substrate or delimited or silicide or oxide or nitride or silicon or germanium or dry or etching or contact or bipolar)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:06

L14	2	6 and (complementary or bipolar or semiconductor or device or collector or emitter or base or region or npn or pnp or transistor or CMOS or FET or doping or type or conductivity or substrate or delimited or silicide or oxide or nitride or silicon or germanium or dry or etching or contact or bipolar)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:06
L15	2	5 and (complementary or bipolar or semiconductor or device or collector or emitter or base or region or npn or pnp or transistor or CMOS or FET or doping or type or conductivity or substrate or delimited or silicide or oxide or nitride or silicon or germanium or dry or etching or contact or bipolar)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:39
L16	2	4 and (complementary or bipolar or semiconductor or device or collector or emitter or base or region or npn or pnp or transistor or CMOS or FET or doping or type or conductivity or substrate or delimited or silicide or oxide or nitride or silicon or germanium or dry or etching or contact or bipolar)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:40
L17	2	3 and (complementary or bipolar or semiconductor or device or collector or emitter or base or region or npn or pnp or transistor or CMOS or FET or doping or type or conductivity or substrate or delimited or silicide or oxide or nitride or silicon or germanium or dry or etching or contact or bipolar)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:42

L18	2	2 and (complementary or bipolar or semiconductor or device or collector or emitter or base or region or npn or pnp or transistor or CMOS or FET or doping or type or conductivity or substrate or delimited or silicide or oxide or nitride or silicon or germanium or dry or etching or contact or bipolar)	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:43
L19	944	257/19	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:43
L20	279	257/274	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:43
L21	3888	257/288	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:43
L22	212	257/279	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:44
L23	7972	257/347	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:44
L24	282	257/277	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:44

L25	110	257/E21.006	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:44
L26	84	257/E21.051	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:44
L27	162	257/E21.32	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:44
L28	37	257/E21.115	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:44
L29	117	257/E21.229	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:44
L30	74	257/E21.245	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:44
L31	132	257/E21.267	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:44
L32	86	257/E21.278	US_PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:45

L33	116	257/E21.293	US-PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:45
L34	602	257/E21.632	US-PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:45
L35	31	"4940671"	US-PGPUB; USPAT; USOOR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/06 13:45

6/6/2010 1:46:15 PM

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